

isc Silicon NPN Power Transistor

2SD111

DESCRIPTION

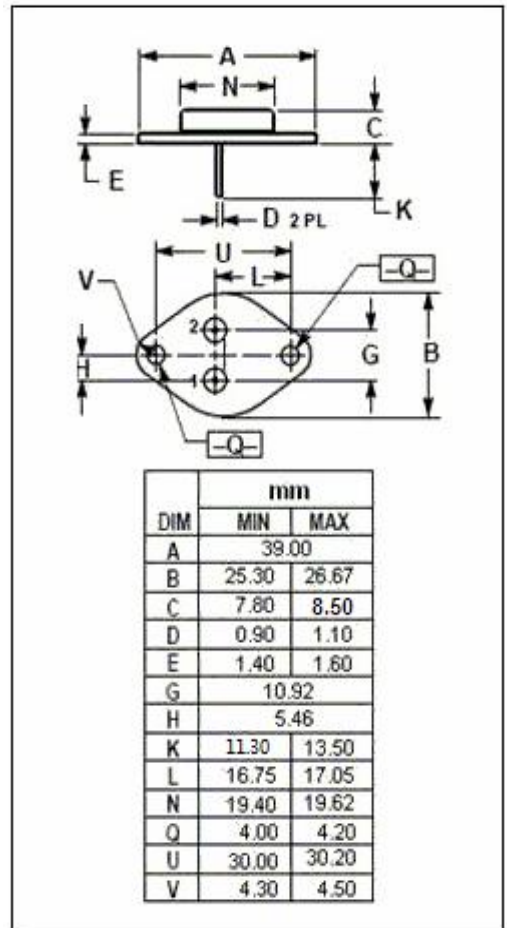
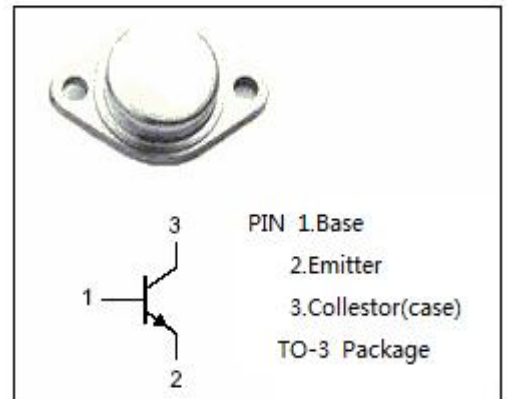
- High Power Dissipation-
: $P_C = 100W @ T_C = 25^\circ C$
- High Current Capability-
: $I_C = 10A$
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for power amplifier , power switching ,DC-DC converter and regulator applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-----------|--|---------|------------|
| V_{CBO} | Collector-Base Voltage | 100 | V |
| V_{CEO} | Collector-Emitter Voltage | 80 | V |
| V_{EBO} | Emitter-Base Voltage | 10 | V |
| I_C | Collector Current-Continuous | 10 | A |
| I_E | Emitter Current-Continuous | 10 | A |
| I_B | Base Current-Continuous | 3 | A |
| P_C | Collector Power Dissipation @ $T_C = 25^\circ C$ | 100 | W |
| T_J | Junction Temperature | 150 | $^\circ C$ |
| T_{stg} | Storage Temperature | -65~150 | $^\circ C$ |



isc Silicon NPN Power Transistor**2SD111****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 10mA ; R _{BE} = ∞ | 80 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 1mA ; I _C = 0 | 10 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 5A; I _B = 1A | | | 1.5 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 5A; I _B = 1A | | | 2.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 50V; I _E = 0 | | | 0.5 | mA |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 10V; I _C =0 | | | 10 | mA |
| h _{FE-1} | DC Current Gain | I _C = 1A; V _{CE} = 5V | 30 | | 300 | |
| h _{FE-2} | DC Current Gain | I _C = 5A; V _{CE} = 5V | 10 | | | |
| f _T | Current-Gain—Bandwidth Product | I _C = 1A ; V _{CE} = 10V | | 1 | | MHz |
| C _{OB} | Output Capacitance | I _E = 0; V _{CB} = 50V; f= 1MHz | | 200 | | pF |

◆ h_{FE-2} Classifications

| R | O | Y |
|-------|--------|---------|
| 30-90 | 50-150 | 100-300 |

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